



January 5 , 2004

Commissioner for Patents
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 28 Davis Avenue
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Subject:	Serial No. 10/697,925 10/30/03
	Seiki Ogura et al.
	TWIN NAND DEVICE STRUCTURE, ARRAY OPERATION AND ITS FABRICATION METHOD

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
 In An Application.

The following Patents and/or Publications are submitted to
 comply with the duty of disclosure under CFR 1.97-1.99 and
 37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
 deposited with the United States Postal Service as first class
 mail in an envelope addressed to: Commissioner for Patents,
 P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

Information in this Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart foreign application. The concise explanation of relevance for the non-English documents is provided therein. A copy of that communication is attached.

Y. Hayashi et al., "Non-volatile Semiconductor Memory and Its Programming Method," JP 11-22940, 12/05/1997, discusses how the ONO layer sandwich stores electron or whole charges in the nitride or interface trap sites.

I. Fujiwara, "Non-volatile Semiconductor Memory and its Read Method," JP 2000-31435, 7/8/1998.

F. Masuoka and R. Shirota et al., "A New NAND Cell for Ultra High Density 5V-Only EEPROMS," May 1988, Proc. 1988 Symp. on VLSI Tech., IV-5, pp. 33-34, describes a floating gate NAND cell that has been used widely as Non-volatile memory.

U.S. Patent 4,943,943 to Hayashi et al., "Read-Out Circuit for Semiconductor Nonvolatile Memory," describes a read-out circuit for a semiconductor nonvolatile memory which is capable of extracting a widely fluctuating output voltage using a reverse read.

U.S. Patent 5,768,192 to Eitan, "Non-Volatile Semiconductor Memory Cell Utilizing Asymmetrical Charge Trapping," discloses a non-volatile semiconductor memory cell utilizing asymmetrical charge trapping.

Sincerely,



Stephen B. Ackerman, Reg. #37761



~~RT0-1449~~

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

JAN 30 2004

(Use several shovels if necessary)

Doctor Number (Specimen)

HALO-01-014B

Appleton Nuclear

10/697, 925

Locality

Seiki Ogura et al.

Ergo Form

10/30/03

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
JP 1	1-2294012/5/97		Japan	H01L	27/115		
JP 0	0-314357/8/98		Japan	H01L	27/115		

OTHER DOCUMENTS (including Author, Title, Date, Portion of Pages, Etc.)

F. Masuoka et al., "A New NAND Cell for Ultra High Density 5V-Only EEPROMs," May 1988, Proc. 1988 Symp. on VLSI Tech, IV-5, pp. 33-34

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.